

ESH1PB, ESH1PC & ESH1PD

Vishay General Semiconductor

High Current Density Surface Mount Ultrafast Rectifiers

eSMP™ Series



DO-220AA (SMP)

MAJOR RATINGS AND CHARACTERISTICS				
I _{F(AV)}	1 A			
V_{RRM}	100 V, 150 V, 200 V			
t _{rr}	25 ns			
V _F	0.90 V			
T _j max.	175 °C			

FEATURES

· Very low profile - typical height of 1.0 mm



- · Ideal for automated placement
- · Glass passivated chip junction
- · Ultrafast recovery times for high frequency
- Low forward voltage drop, low power loss
- · Low thermal resistance
- Meets MSL level 1 per J-STD-020C, LF max peak of 260 °C
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

TYPICAL APPLICATIONS

For use in secondary rectification and freewheeling for ultrafast switching speeds of ac-to-ac and dc-to-dc converters in high temperature conditions for both consumer and automotive applications.

MECHANICAL DATA

Case: DO-220AA (SMP)

Epoxy meets UL-94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002B and JESD22-B102D

E3 suffix for commercial grade, HE3 suffix for high

reliability grade (AEC Q101 qualified)

Polarity: Color band denotes cathode end

MAXIMUM RATINGS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT
Device marking code		PB	PC	PD	
Maximum repetitive peak reverse voltage	V_{RRM}	100	150	200	V
Maximum average forward rectified current (Fig. 1)	I _{F(AV)}	1.0		Α	
Peak forward surge current 10 ms single half sine- wave superimposed on rated load	I _{FSM}	50		А	
Operating junction and storage temperature range	T _J , T _{STG}	- 55 to + 175		°C	

ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Maximum instantaneous forward voltage ⁽¹⁾	at $I_F = 0.7 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$ at $I_F = 1 \text{ A}$, $T_j = 25 ^{\circ}\text{C}$	V _F	0.86 0.90	V	
Maximum reverse current at rated $V_R^{(1)}$ voltage	$T_j = 25 ^{\circ}\text{C}$ $T_j = 125 ^{\circ}\text{C}$	I _R	1.0 25	μΑ	
Maximum reverse current	at V _R = 20 V, T _j = 150 °C	I _R	50	μΑ	

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ELECTRICAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	TEST CONDITIONS	SYMBOL	VALUE	UNIT	
Maximum reverse recovery time	at $I_F = 0.5 \text{ A}$, $I_R = 1 \text{ A}$, $I_{rr} = 0.25 \text{ A}$	t _{rr}	25	ns	
Typical reverse recovery time	at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 25$ °C at $I_F = 1.0$ A, $V_R = 30$ V di/dt = 50 A/ μ s, $I_{rr} = 10$ % I_{RM} $T_j = 100$ °C	t _{rr}	25 35	ns	
Typical reverse recovery time	at I_F = 1.0 A, V_R = 30 V di/dt = 50 A/ μ s, I_{rr} = 10 % I_{RM} T_j = 25 °C at I_F = 1.0 A, V_R = 30 V di/dt = 50 A/ μ s, I_{rr} = 10 % I_{RM} T_j = 100 °C	Q _{rr}	10 15	nC	
Typical junction capacitance	at 4.0 V, 1 MHz	CJ	25	pF	

Note:

(1) Pulse test: 300 μ s pulse width, 1 % duty cycle

THERMAL CHARACTERISTICS (T _A = 25 °C unless otherwise noted)					
PARAMETER	SYMBOL	ESH1PB	ESH1PC	ESH1PD	UNIT
Typical thermal resistance ⁽¹⁾	$egin{array}{c} {\sf R}_{ heta {\sf JA}} \ {\sf R}_{ heta {\sf JL}} \ {\sf R}_{ heta {\sf JC}} \end{array}$		105 15 20		°C/W

Note:

(1) Thermal resistance from junction to ambient and junction to lead mounted on P.C.B. with 5.0 x 5.0 mm copper pad areas. $R_{\theta JL}$ is measured at the terminal of cathode band. $R_{\theta JC}$ is measured at the top centre of the body

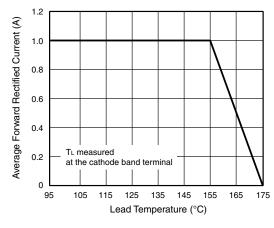
ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
ESH1PB-E3/84A	0.024	84A	3000	7" Diameter Plastic Tape & Reel		
ESH1PB-E3/85A	0.024	85A	10000	13" Diameter Plastic Tape & Reel		
ESH1PBHE3/84A (1)	0.024	84A	3000	7" Diameter Plastic Tape & Reel		
ESH1PBHE3/85A (1)	0.024	85A	10000	13" Diameter Plastic Tape & Reel		

Note:

(1) Automotive grade AEC Q101 qualified

RATINGS AND CHARACTERISTICS CURVES

(T_A = 25 °C unless otherwise noted)





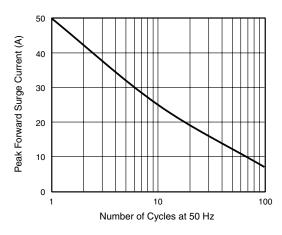


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current

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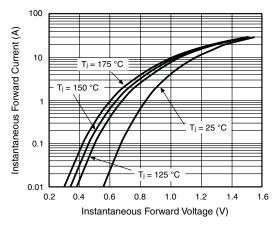


Figure 3. Typical Instantaneous Forward Characteristics

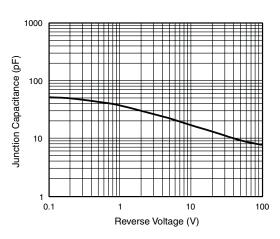


Figure 5. Typical Junction Capacitance

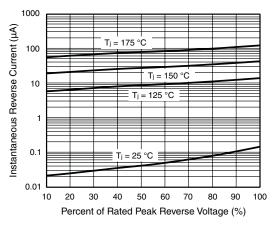


Figure 4. Typical Reverse Leakage Characteristics

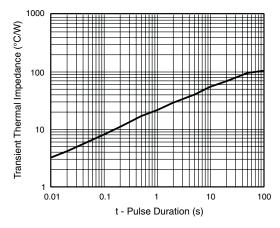
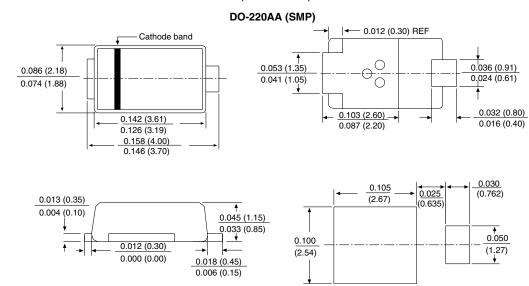


Figure 6. Typical Transient Thermal impedance

PACKAGE OUTLINE DIMENSIONS in inches (millimeters)



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